

Polarization effects in radiation damaged scCVD Diamond detectors

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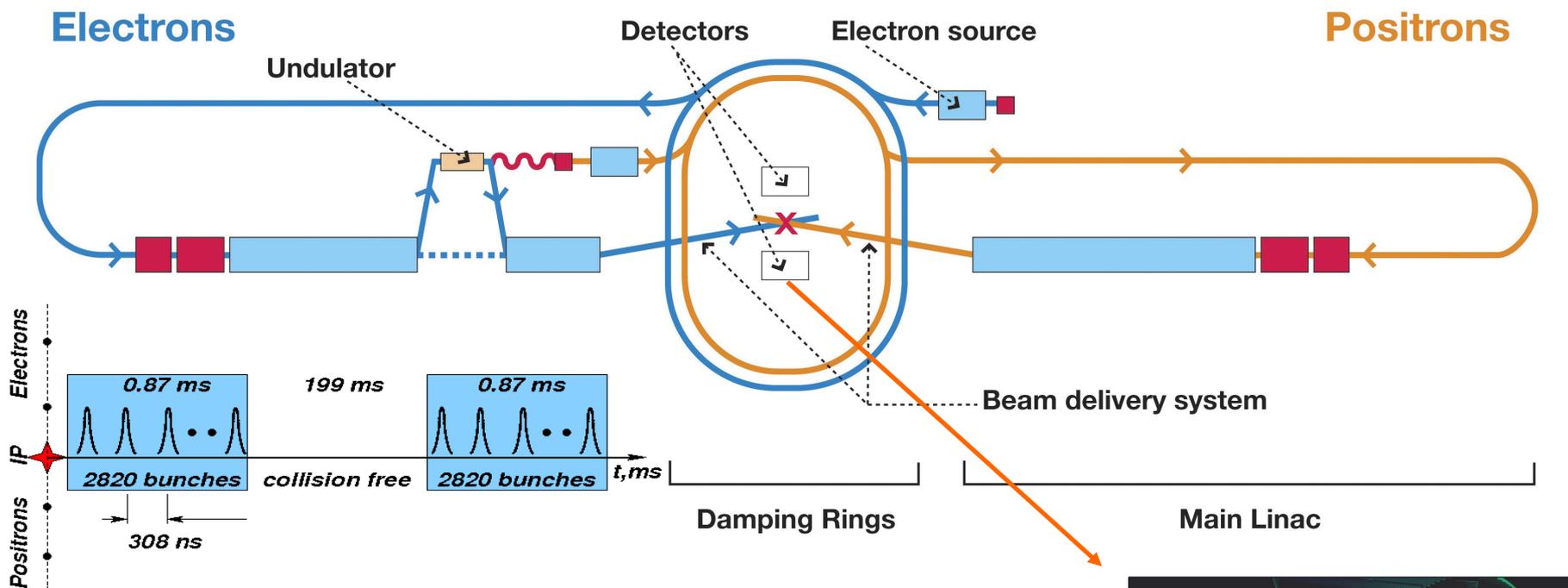
4th NoRHDia Workshop @ GSI

- Why do we need Diamond Detector @ ILC?
- BeamCal challenge
- Diamond properties
- Charge collection
 - Ideal crystal, Radiation damaged crystal
- Polarization creation, model
- Experimental studies:
 - CCD vs Dose, CCD time dependence
 - Future plans
- Summary



The International Linear Collider

~30km



Parameters:

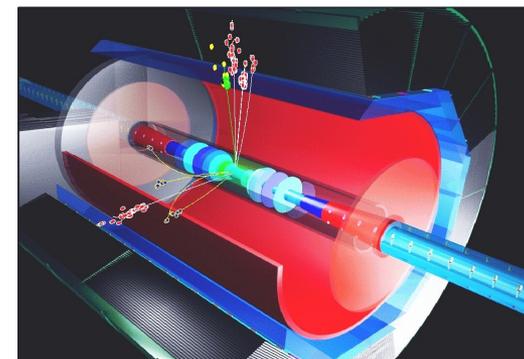
500 GeV (1 TeV upgrade possible)

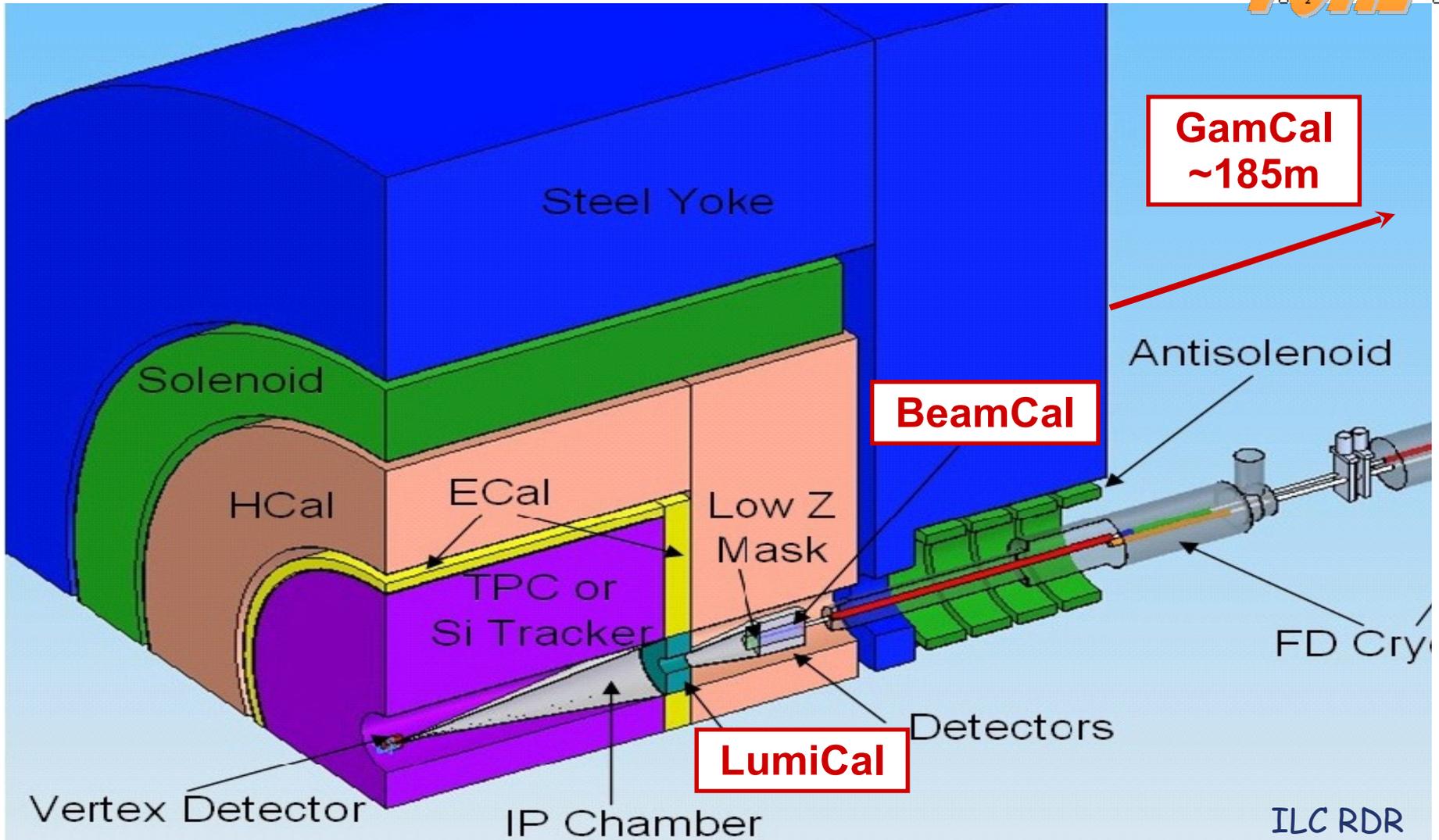
$2 \times 10^{34} \text{ cm}^{-2}\text{sec}^{-1}$

electron polarization ~80 %

positron polarization ~30 % (60 %)

beam sizes: $\sigma_x \approx 600\text{nm}$, $\sigma_y \approx 6\text{nm}$, $\sigma_z = 300\mu\text{m}$





- Compact em calorimeter with sandwich structure:

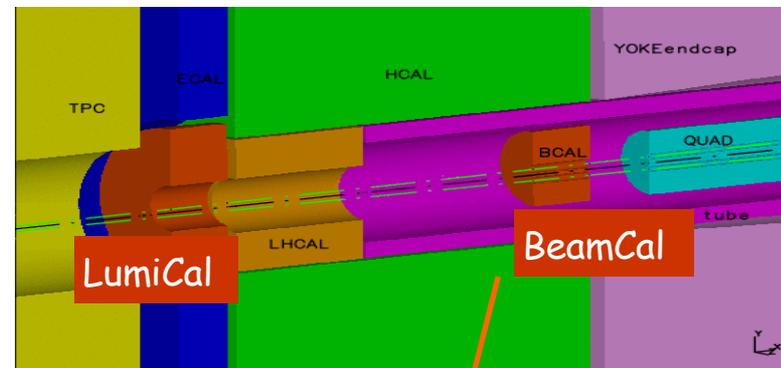
- 30 layers of $1 X_0$

- 3.5mm W and 0.3mm sensor

- ★ Angular coverage from $\sim 5\text{mrad}$ to $\sim 45\text{mrad}$

- ★ Molière radius $R_M \approx 1\text{cm}$

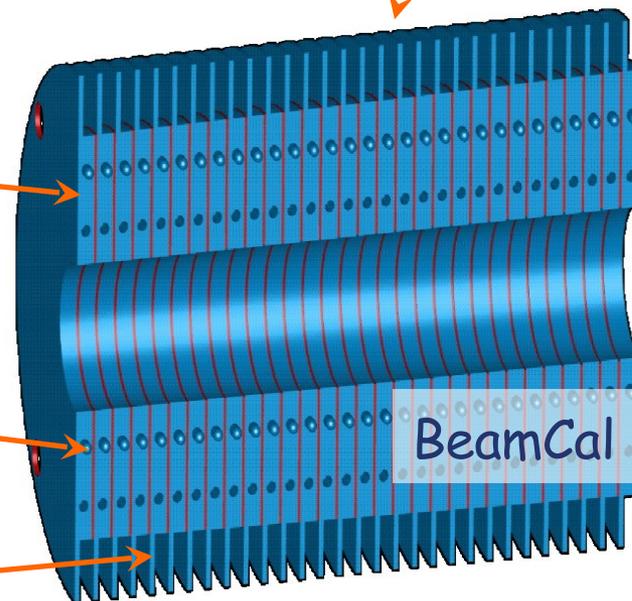
- ★ Segmentation between 0.5 and $0.8 \times R_M$



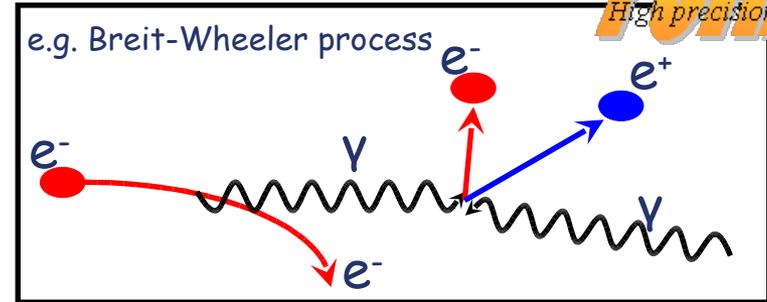
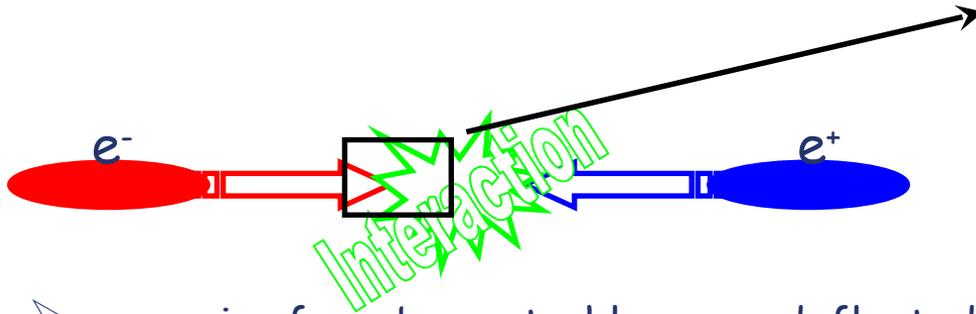
W absorber layers

Radiation hard sensors with thin readout planes

Space for readout electronics



Creation of beamstrahlung at the ILC



➤ e^+e^- pairs from beamstrahlung are deflected into the BeamCal

➤ 15000 e^+e^- per BX

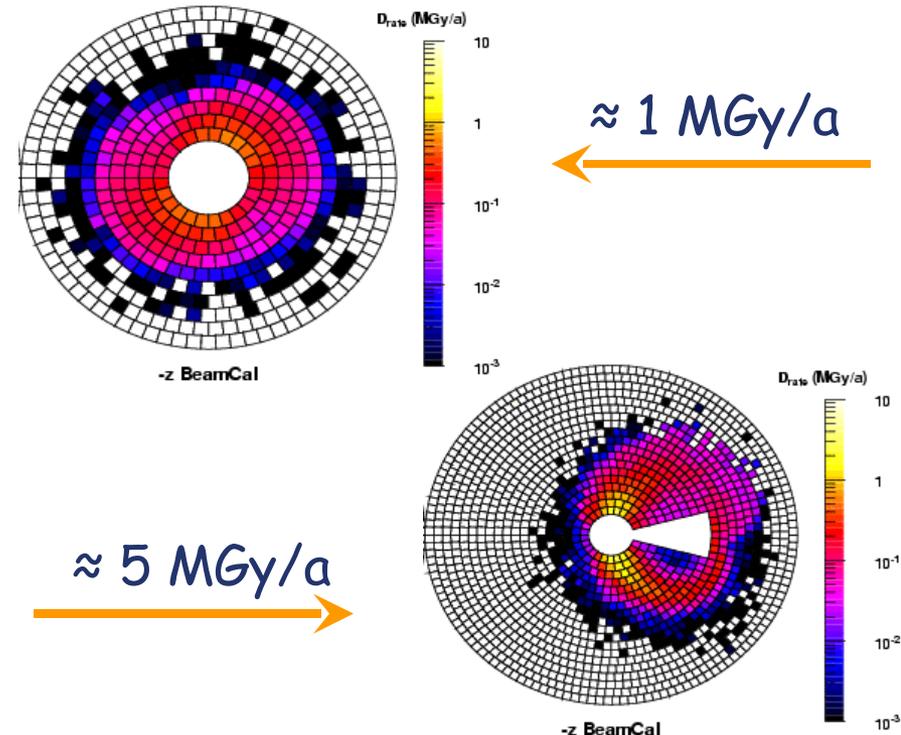
⇒ 10 - 20 TeV total energy dep.

➤ ~ 10 MGy per year strongly dependent on the beam and magnetic field configuration

⇒ radiation hard sensors

➤ Detect the signature of single high energetic particles on top of the background.

⇒ high dynamic range/linearity.



Diamond properties

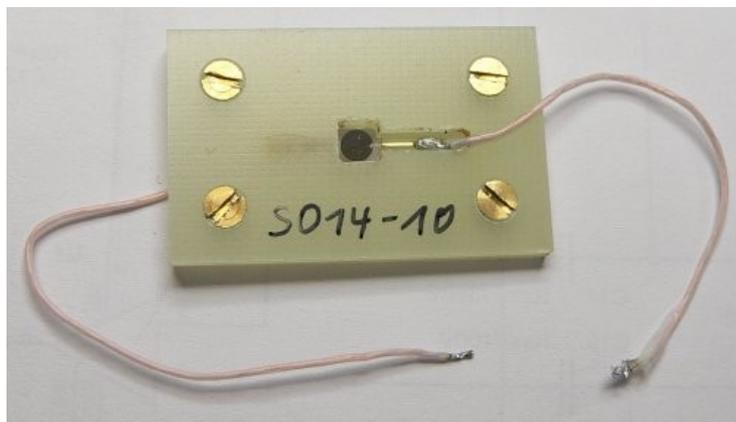
- Density 3.52 g cm^{-3}
- Dielectric constant 5.7
- Breakdown field 10^7 V cm^{-1}
- Resistivity $>10^{11} \Omega \text{ cm}$
- Band Gap 5.5 eV
- Electron mobility 1800 (4500) $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$
- Hole mobility 1200 (3800) $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$
- Energy to create e-h pair 13.1 eV
- Average signal created $36 \text{ e } \mu\text{m}^{-1}$

* High-purity single crystal CVD

Sensors

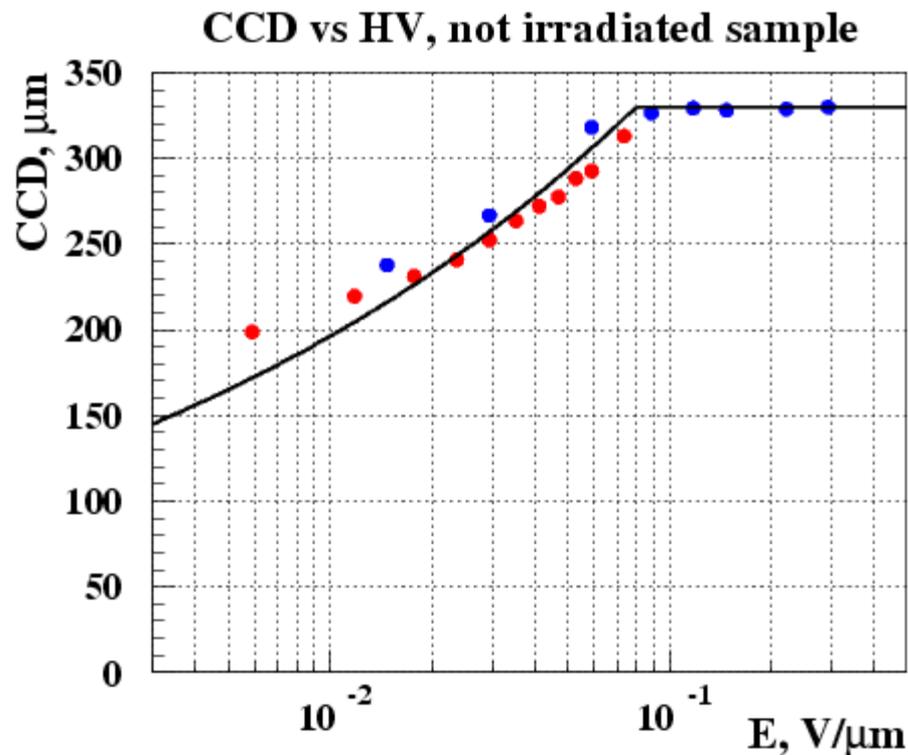
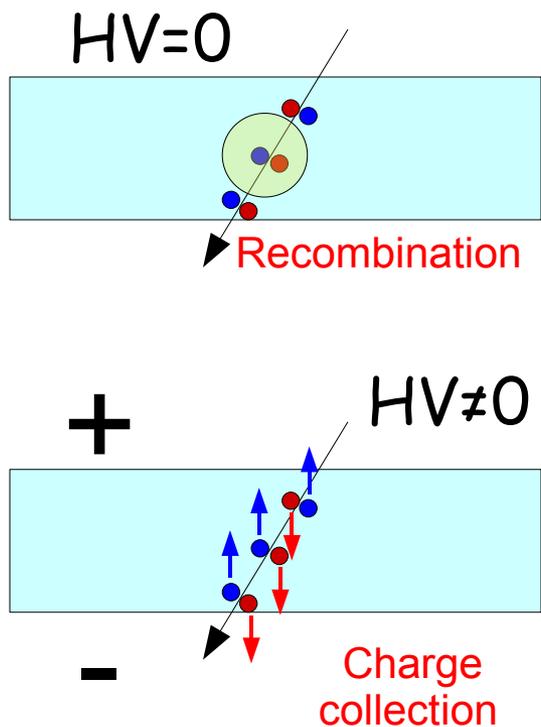
sc CVD diamond from Element 6
(provided by GSI, Darmstadt)

Thickness 326 μm , active area 3mm in diameter



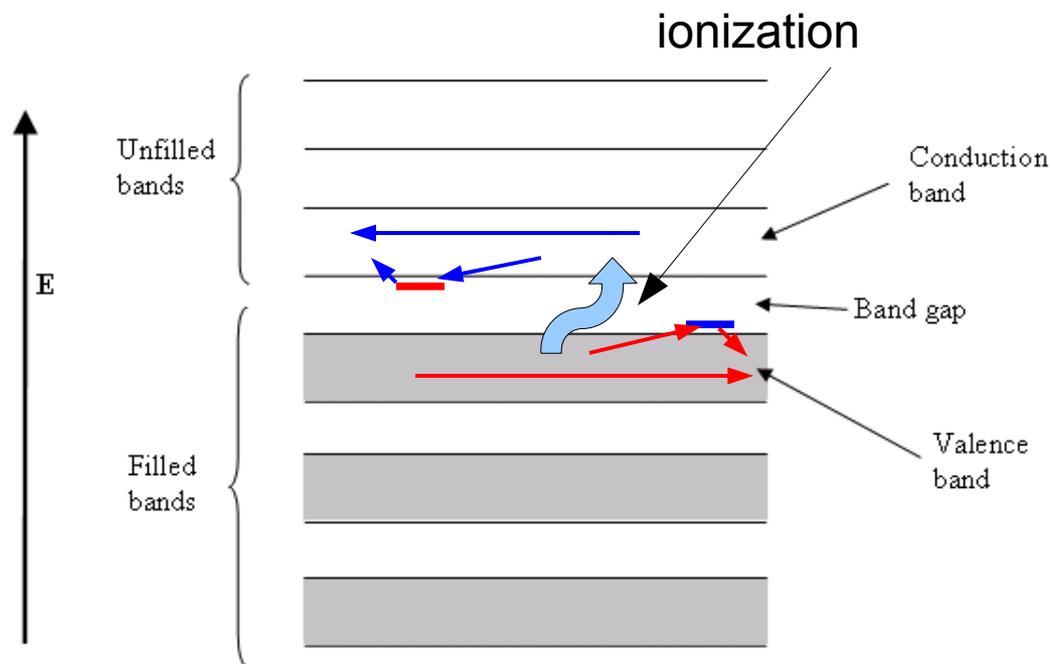
2 sensors, one is irradiated up to 5 MGy dose
at the 10 MeV electron beam in 2007

- Charge collection efficiency depends on E



- Radiation causes local damages of the lattice structure.
- These local damages (traps) are able to capture free charge carriers and release them after some time

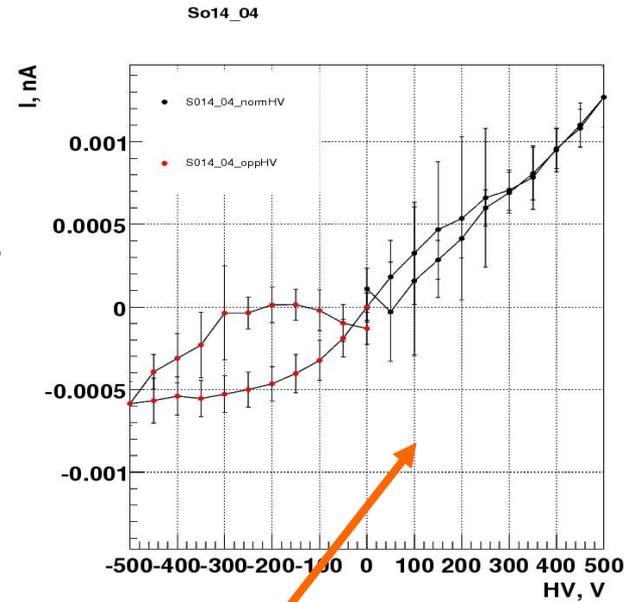
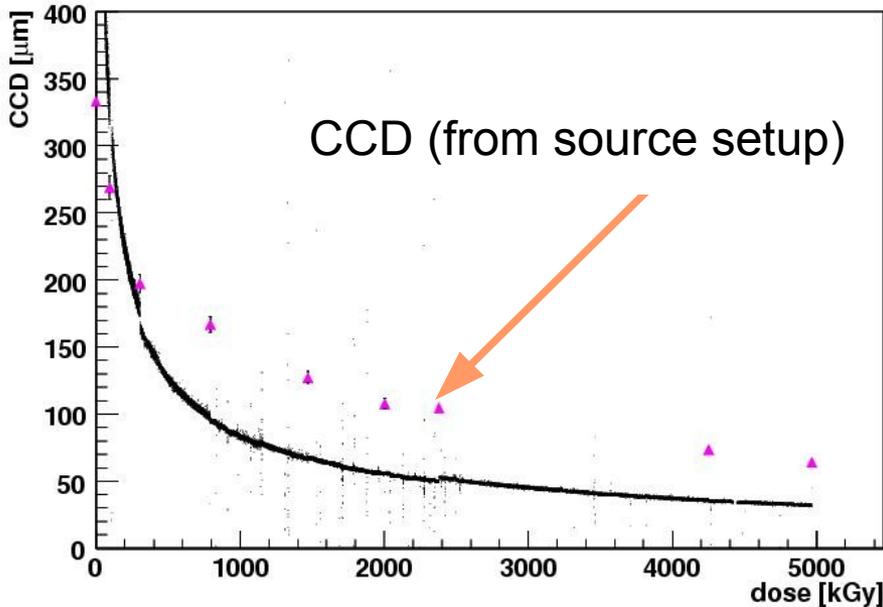
- **Assumptions:**
- **Trap density is uniform (bulk radiation damage)**
- **Traps are created independently (linearity vs dose)**



After absorbing 5 MGy:

CVD diamonds still operational.

CCD (from I_{sens}) vs dose

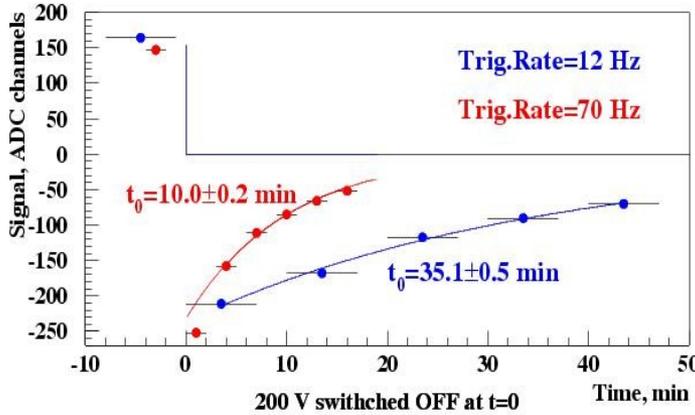
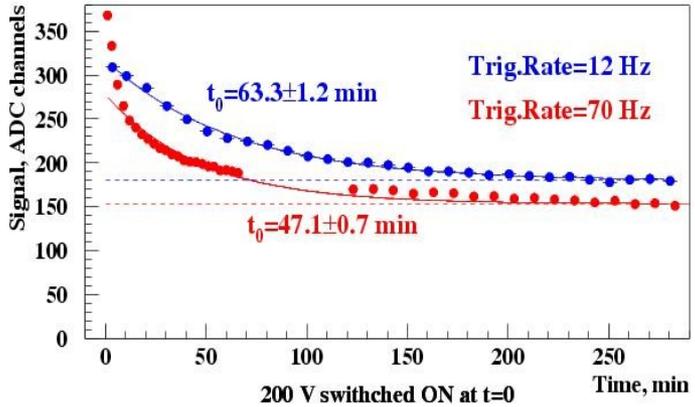


- Very low leakage currents (\sim pA) after the irradiation.
- Decrease of the charge collection distance with the dose.
- Generation of trapping centers due to irradiation. **Traps release?**
- **Strong polarization effects !!!**

After absorbing 5 MGy:

Measurements at ^{90}Sr -source setup:

So14-04 Diamond Sample



After switching HV on signal drops with time

Switching HV off after signal stabilization: strong signal of opposite polarity is observed

Signal time behavior depends on the MIPs rate

Dynamic polarization !

Polarization Model

Radiation damage – uniformly produced traps

MIP signal – uniformly produced e-h pairs

+Electric field → **NONUNIFORM** space charge

Change of the electric field

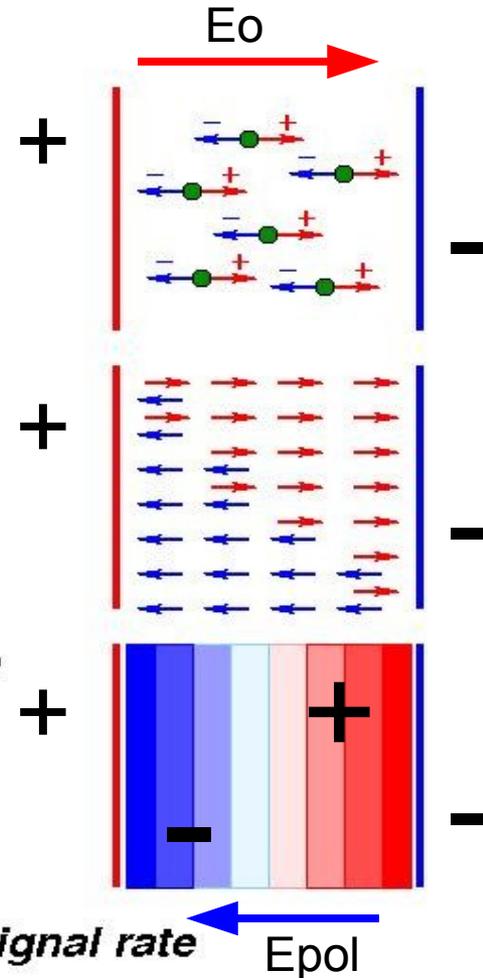
e-h Recombination if the field is low

Release of trapped charges (decay time)

Change of the space charge distribution

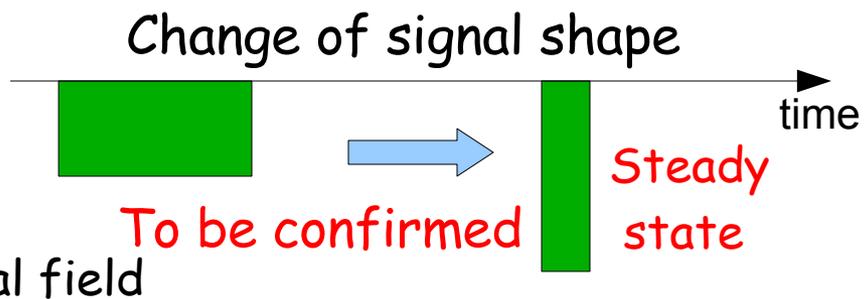
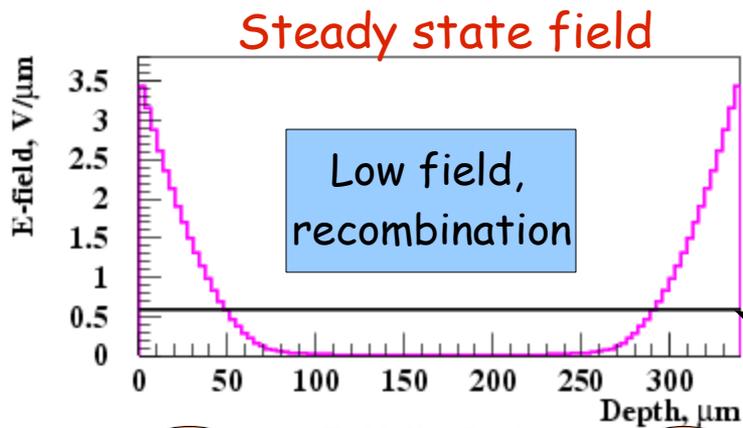
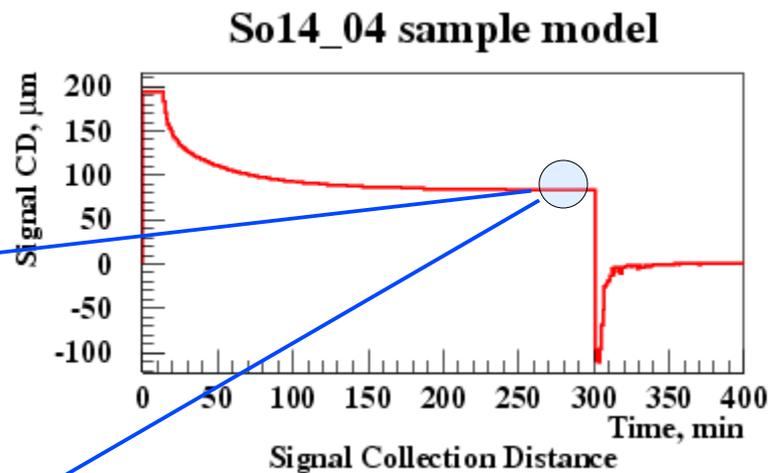
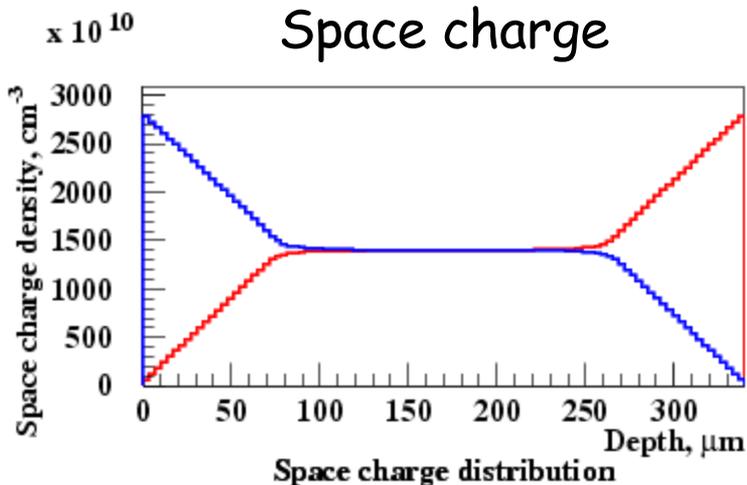
Steady state POLARIZATION

Dependent on trap density, applied voltage and signal rate



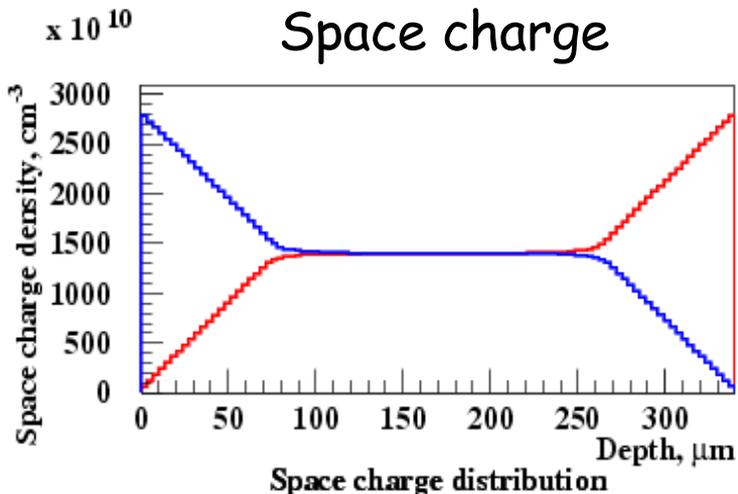
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Model of sCVD Diamond Polarization - 1

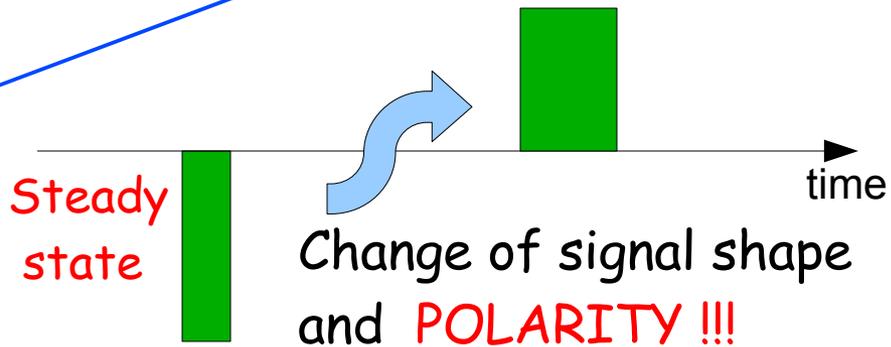
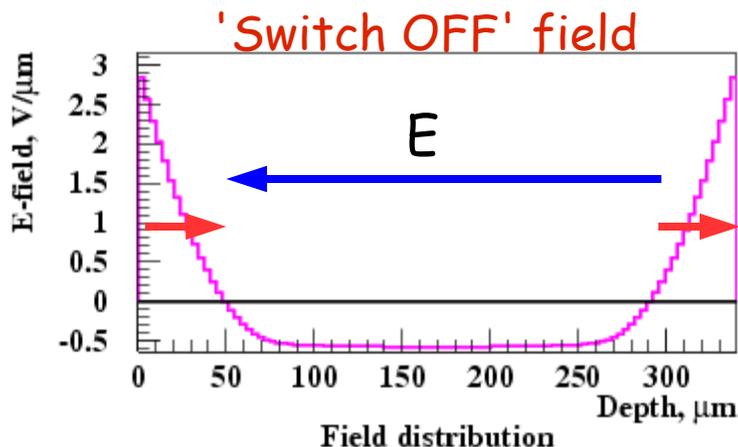
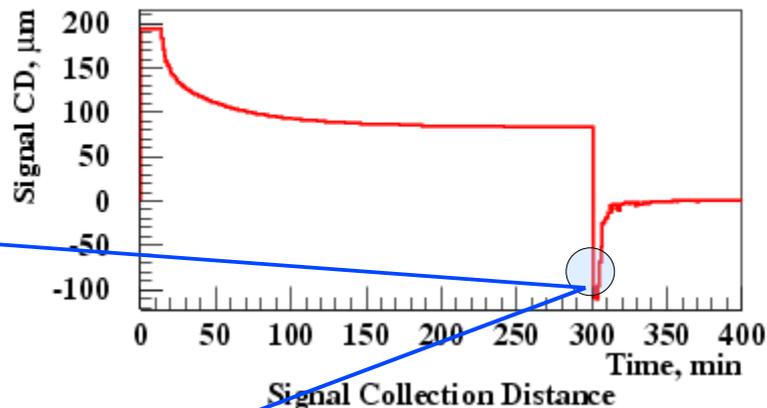


Model of sCVD Diamond Polarization - 2

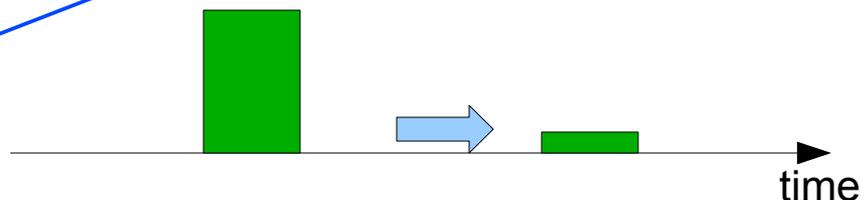
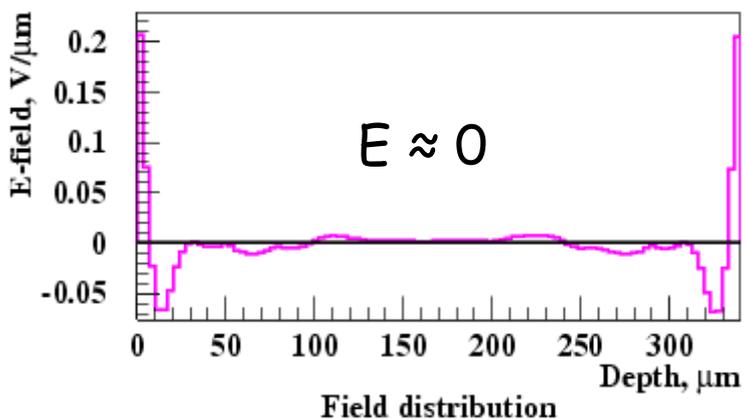
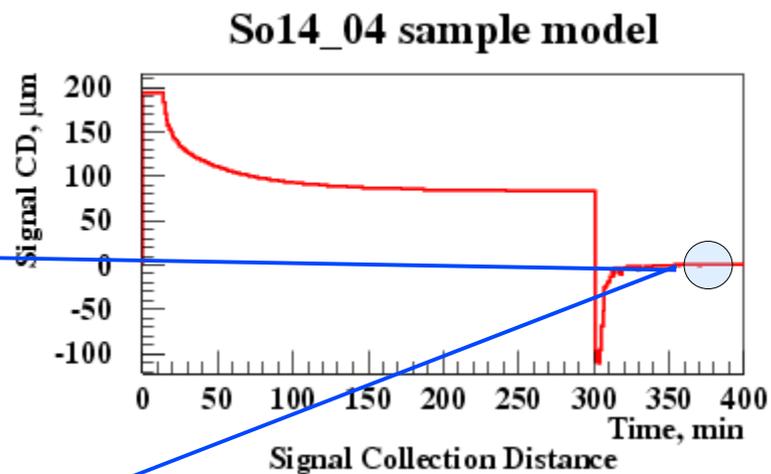
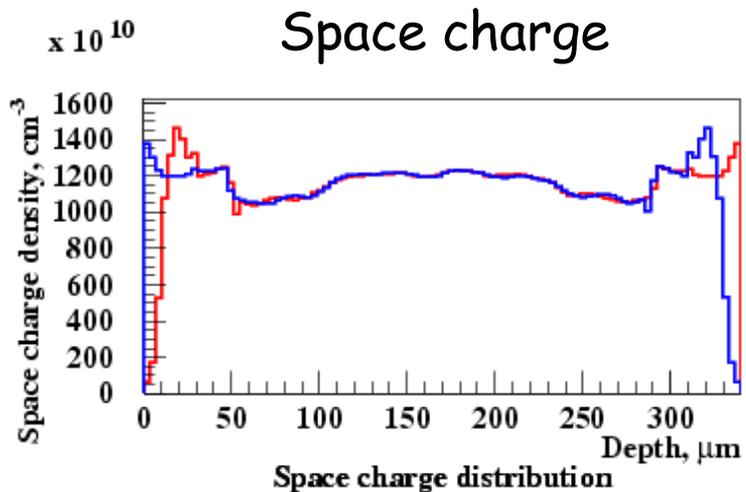
HV \rightarrow 0 !



So14_04 sample model



HV = 0



Change of signal size



⁹⁰Sr setup: CCD time dependence

➤ Diamond sCVD sensor after 5 MGy

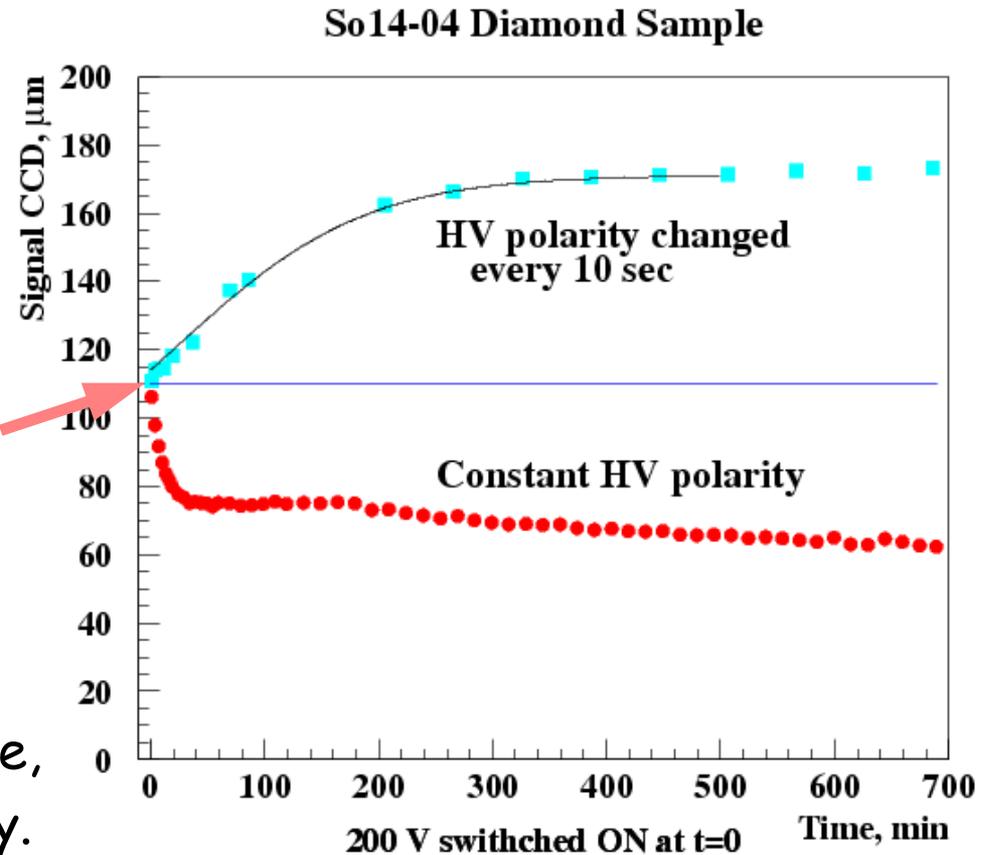
$$CCE_0 = \frac{2}{aD} \cdot \left(1 - \frac{1 - \exp(-aD)}{aD} \right)$$

$$a = \frac{\pi R_{trap}^2}{l_0} \cdot \frac{n_{free}}{N}$$

CCD at t=0 allows
to extract $n_{trap} R_{trap}^2$ value

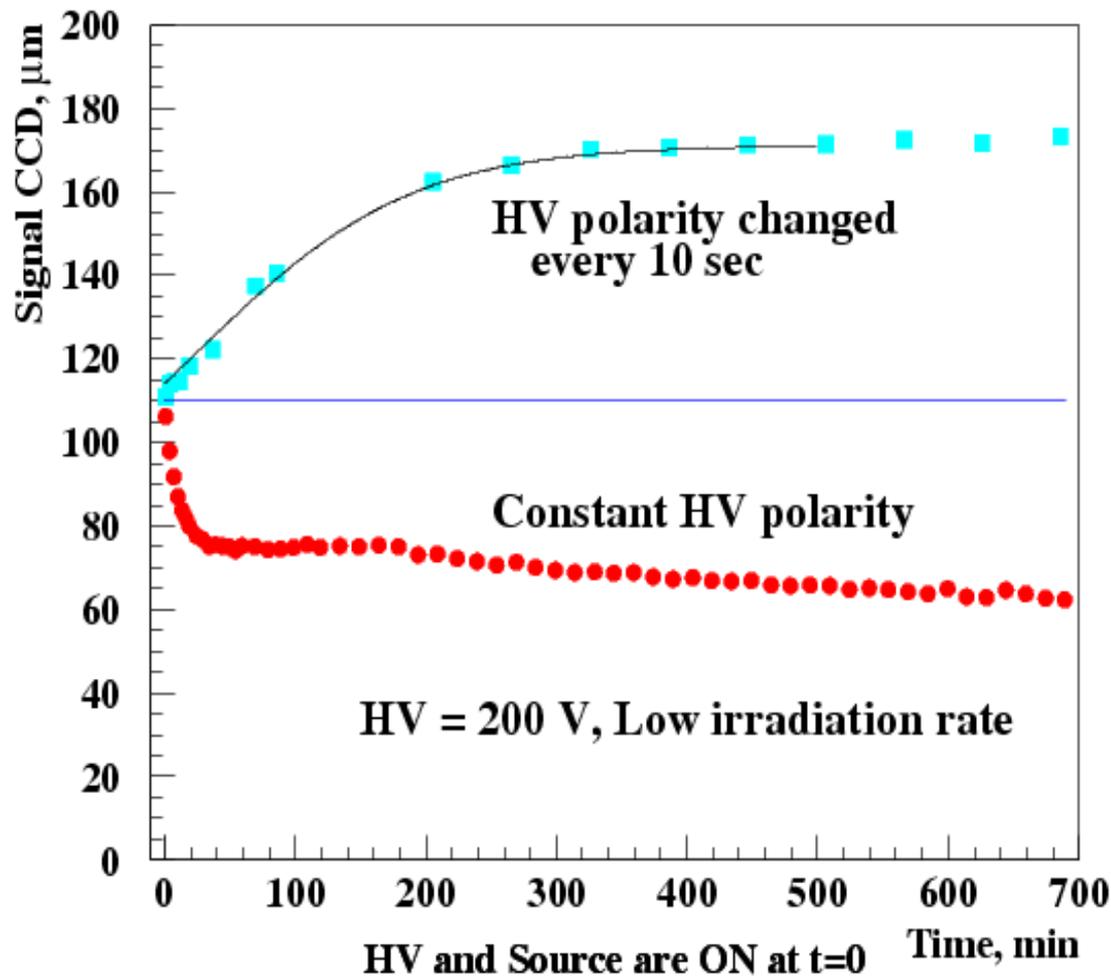
Steady state CCD is sensitive
to n_{trap} , T_0 and signal rate

Curve shape depends on the rate,
trap properties and trap density.

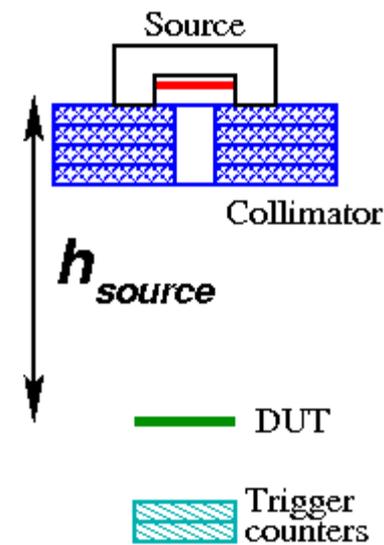


CCD vs time dependence, low rate

So14-04 Diamond Sample (5 MGy)

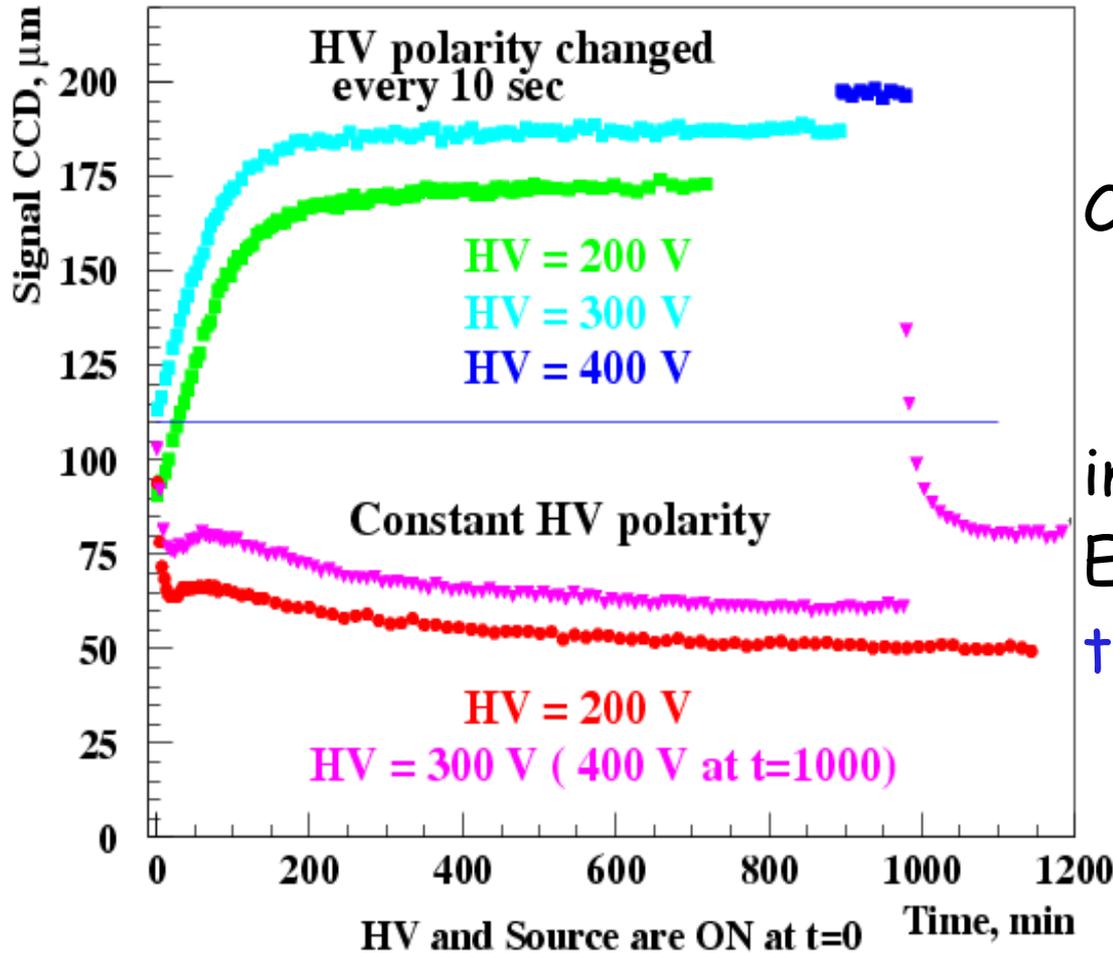


Trigger rate
about 12 Hz,
old trigger
counters,
 $h_{\text{Source}} \sim 36 \text{ mm}$



CCD vs time, different HV

So14-04 Diamond Sample (5 MGy)

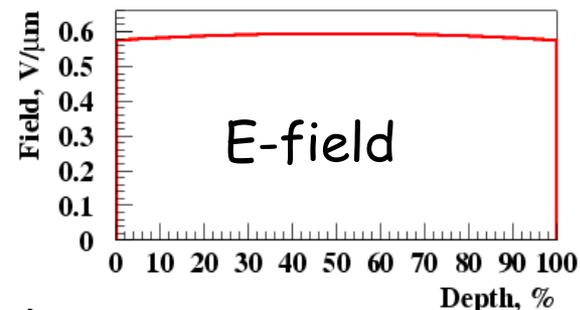
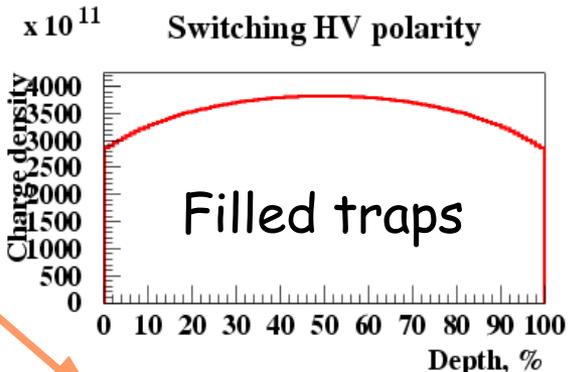
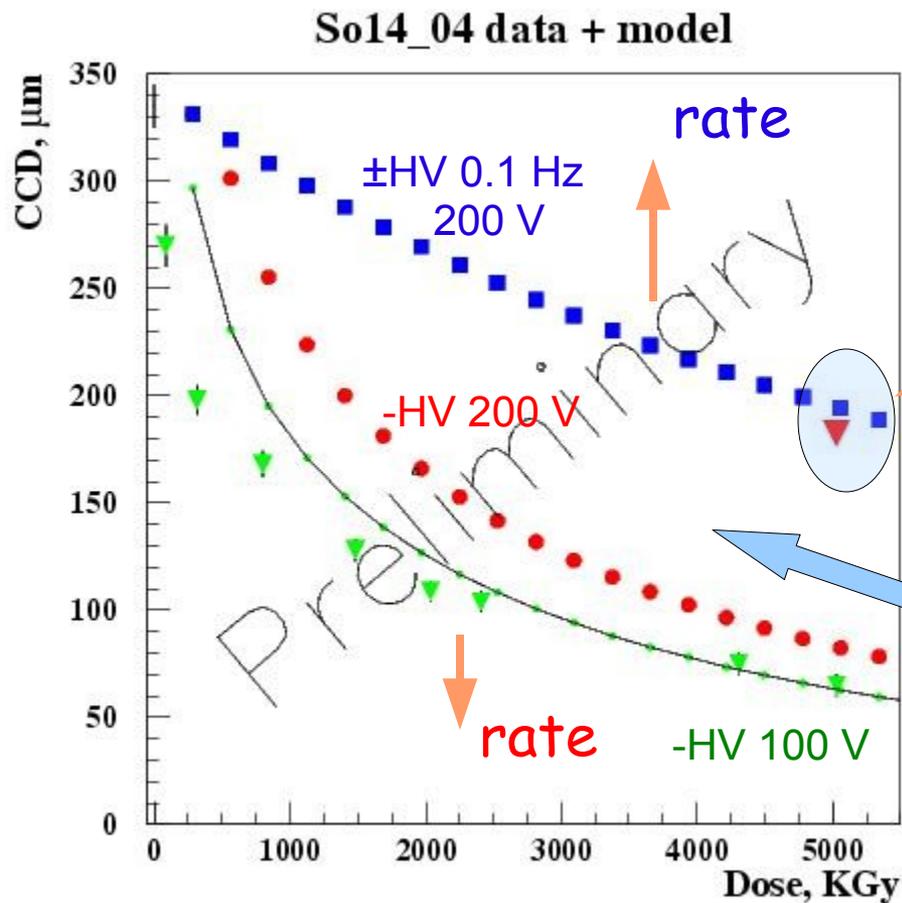


"High rate" data

CCD dependence on HV in case of switching polarity is **NOT** yet in the model. What is E-field dependent: trap release time, capture probability?

Irradiated single crystal CVD Diamond

Regular change of HV polarity to avoid polarization: almost uniform E-field



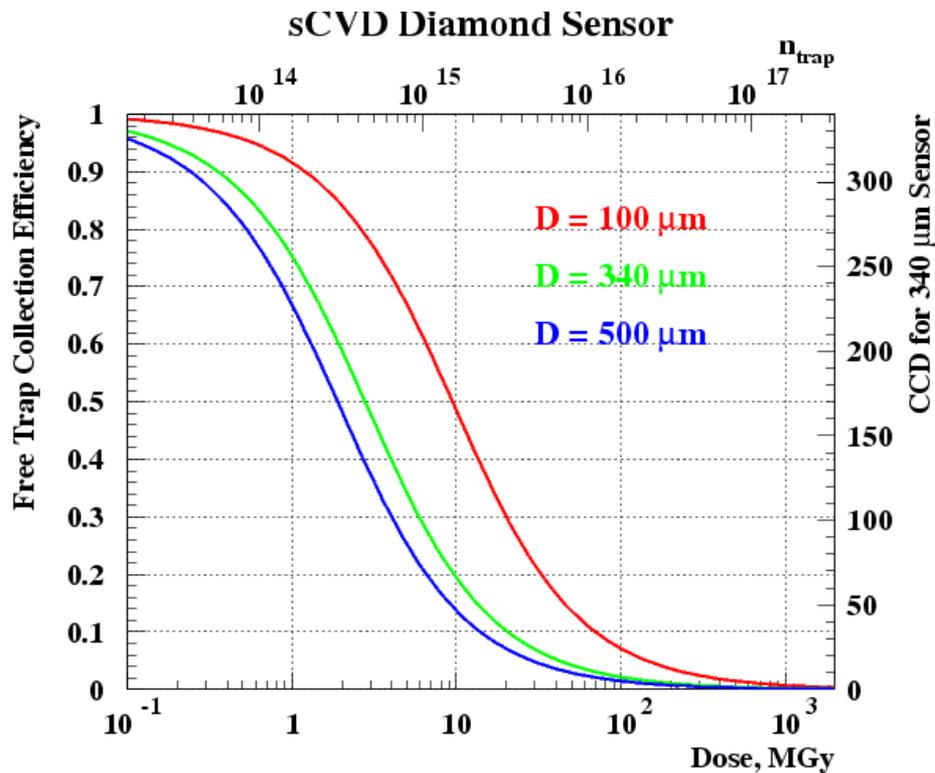
$$n_{\text{traps}} = k \text{ Dose} + n_0 ?$$

More experimental studies needed

Charge absorption probability for the thin layer:

$$P_l = 1 - \exp\left(-\pi R_{trap}^2 \cdot \frac{l}{l_0} \cdot \frac{n_{free}}{N}\right) = 1 - e^{-al}$$

$$a = \frac{\pi R_{trap}^2}{l_0} \cdot \frac{n_{free}}{N}$$



In case when free traps are uniformly distributed:

Charge collection efficiency could be calculated analytically. For the detector of thickness D:

$$CCE_0 = \frac{2}{aD} \cdot \left(1 - \frac{1 - \exp(-aD)}{aD}\right)$$

- Strong polarization effect is observed in the radiation damaged scCVD Diamond detector.
- It was shown that the polarization significantly decreases the detector charge collection efficiency.
- A simple model is developed in order to understand and describe observed phenomena.
- Method of routinely switching HV polarity is proposed to suppress polarization. Large improvement of CCE is observed experimentally.
- More work is needed to understand CCD dependence on the signal rate and details of polarization development.
- It is desirable to continue test beam studies up to higher doses (approx 50 MGy) and measure sensor CCD @ ILC-like conditions.

Thank you...

Special thanks to GSI team:
CVDD sensors, test beam etc.



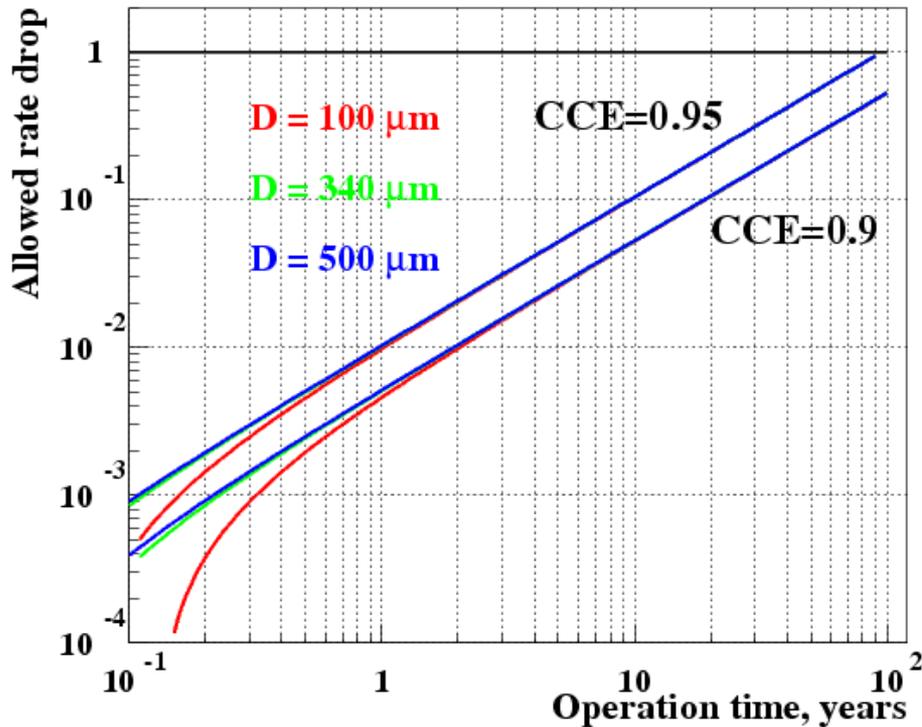
Uniformly (partly) filled traps

Allowed reduction of the flux keeping ϵ efficiency:

$$r = \frac{\Phi_\epsilon}{\Phi_{nom}} = \frac{1}{R_{nom}^q} \cdot \frac{Q}{T_0 \cdot Q_{absorb}} \cdot \left(t - \frac{n_{free}^\epsilon}{R_{trap}} \right)$$

; t – detector operation time

sCVD Diamond Sensor



Alternating HV polarity +
+ stable particle flux =
= XXL radiation hardness

Charge collection efficiency
could be kept at high level
for a very long time if particle
flux is maintained stable.

Leakage current ???
Crystal destruction ???